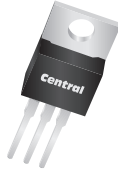


2N5294  
2N5296  
2N5298

**NPN SILICON TRANSISTOR**



**TO-220 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N5294, 2N5296, and 2N5298 types are NPN silicon transistors manufactured by the epitaxial base process, and designed for applications that require power amplifier and medium speed switching capabilities.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_C=25^\circ\text{C}$ )

|  |
|--|
| Collector-Base Voltage                           |
| Collector-Emitter Voltage                        |
| Collector-Emitter Voltage ( $R_{BE}=100\Omega$ ) |
| Collector-Emitter Voltage                        |
| Continuous Collector Current                     |
| Continuous Base Current                          |
| Power Dissipation                                |
| Operating and Storage Junction Temperature       |
| Thermal Resistance                               |
| Thermal Resistance                               |

| SYMBOL         | <u>2N5294</u> | <u>2N5296</u> | <u>2N5298</u> | UNITS              |
|----------------|---------------|---------------|---------------|--------------------|
| $V_{CBO}$      | 80            | 60            | 80            | V                  |
| $V_{CEV}$      | 80            | 60            | 80            | V                  |
| $V_{CER}$      | 75            | 50            | 70            | V                  |
| $V_{CEO}$      | 70            | 40            | 60            | V                  |
| $I_C$          |               | 4.0           |               | A                  |
| $I_B$          |               | 2.0           |               | A                  |
| $P_D$          |               | 36            |               | W                  |
| $T_J, T_{stg}$ |               | -65 to +150   |               | $^\circ\text{C}$   |
| $\theta_{JA}$  |               | 70            |               | $^\circ\text{C/W}$ |
| $\theta_{JC}$  |               | 3.47          |               | $^\circ\text{C/W}$ |

**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

| SYMBOL        | TEST CONDITIONS                                       | <u>2N5294</u> |     | <u>2N5296</u> |     | <u>2N5298</u> |     | UNITS |
|---------------|---|---------------|-----|---------------|-----|---------------|-----|-------|
|               |   | MIN           | MAX | MIN           | MAX | MIN           | MAX |       |
| $I_{CEV}$     | $V_{CE}=35V, V_{EB}=1.5V$                             | -             | -   | -             | 2.0 | -             | -   | mA    |
| $I_{CEV}$     | $V_{CE}=35V, V_{EB}=1.5V, T_C=150^\circ\text{C}$      | -             | -   | -             | 5.0 | -             | -   | mA    |
| $I_{CEV}$     | $V_{CE}=65V, V_{EB}=1.5V$                             | -             | 0.5 | -             | -   | -             | 0.5 | mA    |
| $I_{CEV}$     | $V_{CE}=65V, V_{EB}=1.5V, T_C=150^\circ\text{C}$      | -             | 3.0 | -             | -   | -             | 3.0 | mA    |
| $I_{CER}$     | $V_{CE}=50V, R_{BE}=100\Omega$                        | -             | 0.5 | -             | -   | -             | 0.5 | mA    |
| $I_{CER}$     | $V_{CE}=50V, R_{BE}=100\Omega, T_C=150^\circ\text{C}$ | -             | 2.0 | -             | -   | -             | 2.0 | mA    |
| $I_{EBO}$     | $V_{EB}=7.0V$   | -             | 1.0 | -             | -   | -             | -   | mA    |
| $I_{EBO}$     | $V_{EB}=5.0V$   | -             | -   | -             | 1.0 | -             | 1.0 | mA    |
| $BV_{CEV}$    | $V_{BE}=1.5V, I_C=100\text{mA}$                       | 80            | -   | 60            | -   | 80            | -   | V     |
| $BV_{CER}$    | $I_C=100\text{mA}, R_{BE}=100\Omega$                  | 75            | -   | 50            | -   | 70            | -   | V     |
| $BV_{CEO}$    | $I_C=100\text{mA}$                                    | 70            | -   | 40            | -   | 60            | -   | V     |
| $V_{CE(SAT)}$ | $I_C=500\text{mA}, I_B=50\text{mA}$                   | -             | 1.0 | -             | -   | -             | -   | V     |
| $V_{CE(SAT)}$ | $I_C=1.0A, I_B=100\text{mA}$                          | -             | -   | -             | 1.0 | -             | -   | V     |
| $V_{CE(SAT)}$ | $I_C=1.5A, I_B=150\text{mA}$                          | -             | -   | -             | -   | -             | 1.0 | V     |
| $V_{BE(ON)}$  | $V_{CE}=4.0V, I_C=500\text{mA}$                       | -             | 1.1 | -             | -   | -             | -   | V     |
| $V_{BE(ON)}$  | $V_{CE}=4.0V, I_C=1.0A$                               | -             | -   | -             | 1.3 | -             | -   | V     |
| $V_{BE(ON)}$  | $V_{CE}=4.0V, I_C=1.5A$                               | -             | -   | -             | -   | -             | 1.5 | V     |

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2N5294  
2N5296  
2N5298

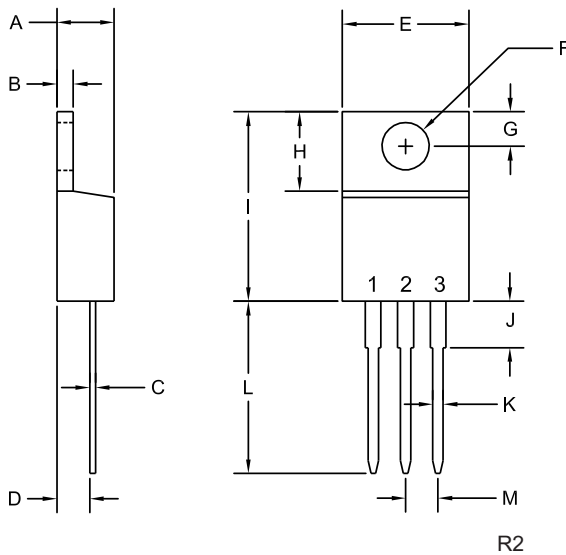
NPN SILICON TRANSISTOR



**ELECTRICAL CHARACTERISTICS - Continued:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

| SYMBOL    | TEST CONDITIONS                   | 2N5294 |     | 2N5296 |     | 2N5298 |     | UNITS   |
|-----------|-----------------------------------|--------|-----|--------|-----|--------|-----|---------|
|           |                                   | MIN    | MAX | MIN    | MAX | MIN    | MAX |         |
| $h_{FE}$  | $V_{CE}=4.0V, I_C=500mA$          | 30     | 120 | -      | -   | -      | -   |         |
| $h_{FE}$  | $V_{CE}=4.0V, I_C=1.0A$           | -      | -   | 30     | 120 | -      | -   |         |
| $h_{FE}$  | $V_{CE}=4.0V, I_C=1.5A$           | -      | -   | -      | -   | 20     | 80  |         |
| $f_T$     | $V_{CE}=4.0V, I_C=200mA$          | 0.8    | -   | 0.8    | -   | 0.8    | -   | MHz     |
| $t_{on}$  | $V_{CC}=30V, I_C=500mA, I_B=50mA$ | -      | 5.0 | -      | -   | -      | -   | $\mu s$ |
| $t_{on}$  | $V_{CC}=30V, I_C=1.0A, I_B=100mA$ | -      | -   | -      | 5.0 | -      | -   | $\mu s$ |
| $t_{on}$  | $V_{CC}=30V, I_C=1.5A, I_B=150mA$ | -      | -   | -      | -   | -      | 5.0 | $\mu s$ |
| $t_{off}$ | $V_{CC}=30V, I_C=500mA, I_B=50mA$ | -      | 15  | -      | -   | -      | -   | $\mu s$ |
| $t_{off}$ | $V_{CC}=30V, I_C=1.0A, I_B=100mA$ | -      | -   | -      | 15  | -      | -   | $\mu s$ |
| $t_{off}$ | $V_{CC}=30V, I_C=1.5A, I_B=150mA$ | -      | -   | -      | -   | -      | 15  | $\mu s$ |

**TO-220 CASE - MECHANICAL OUTLINE**



| SYMBOL  | DIMENSIONS |       |             |       |
|---------|------------|-------|-------------|-------|
|         | INCHES     |       | MILLIMETERS |       |
|         | MIN        | MAX   | MIN         | MAX   |
| A       | 0.170      | 0.190 | 4.31        | 4.82  |
| B       | 0.045      | 0.055 | 1.15        | 1.39  |
| C       | 0.013      | 0.026 | 0.33        | 0.65  |
| D       | 0.083      | 0.107 | 2.10        | 2.72  |
| E       | 0.394      | 0.417 | 10.01       | 10.60 |
| F (DIA) | 0.140      | 0.157 | 3.55        | 4.00  |
| G       | 0.100      | 0.118 | 2.54        | 3.00  |
| H       | 0.230      | 0.270 | 5.85        | 6.85  |
| I       | 0.560      | 0.625 | 14.23       | 15.87 |
| J       | -          | 0.250 | -           | 6.35  |
| K       | 0.025      | 0.038 | 0.64        | 0.96  |
| L       | 0.500      | 0.579 | 12.70       | 14.70 |
| M       | 0.090      | 0.110 | 2.29        | 2.79  |

TO-220 (REV: R2)

**LEAD CODE:**

- 1) Base
- 2) Collector
- 3) Emitter
- Tab) Collector

**MARKING: FULL PART NUMBER**

R1 (26-September 2012)

## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

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[www.centrasemi.com](http://www.centrasemi.com)

**Worldwide Field Representatives:**  
[www.centrasemi.com/wwreps](http://www.centrasemi.com/wwreps)

**Worldwide Distributors:**  
[www.centrasemi.com/wwdistributors](http://www.centrasemi.com/wwdistributors)

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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**Факс:** 8 (812) 320-02-42

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